



**ALPHA & OMEGA**  
SEMICONDUCTOR



**AOP607**

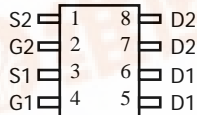
**Complementary Enhancement Mode Field Effect Transistor**

**General Description**

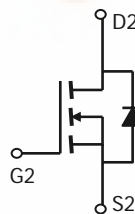
The AOP607 uses advanced trench technology MOSFETs to provide excellent  $R_{DS(ON)}$  and low gate charge. The complementary MOSFETs may be used in H-bridge, Inverters and other applications. *Standard Product AOP607 is Pb-free (meets ROHS & Sony 259 specifications). AOP607L is a Green Product ordering option. AOP607 and AOP607L are electrically identical.*

**Features**

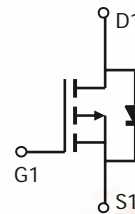
n-channel	p-channel
$V_{DS} (V) = 60V$	-60V
$I_D = 4.7A (V_{GS}=10V)$	-3.4A ( $V_{GS}=-10V$ )
$R_{DS(ON)}$	$R_{DS(ON)}$
$< 56m\Omega (V_{GS}=10V)$	$< 105m\Omega (V_{GS}=-10V)$
$< 77m\Omega (V_{GS}=4.5V)$	$< 135m\Omega (V_{GS}=-4.5V)$



PDIP-8



n-channel



p-channel

**Absolute Maximum Ratings  $T_A=25^\circ C$  unless otherwise noted**

Parameter	Symbol	Max n-channel	Max p-channel	Units
Drain-Source Voltage	$V_{DS}$	60	-60	V
Gate-Source Voltage	$V_{GS}$	$\pm 20$	$\pm 20$	V
Continuous Drain Current <sup>A</sup>	$T_A=25^\circ C$	4.7	-3.4	A
		$T_A=70^\circ C$	3.8	
Pulsed Drain Current <sup>B</sup>	$I_{DM}$	20	-20	
Power Dissipation	$T_A=25^\circ C$	2.5	2.5	W
		$T_A=70^\circ C$	1.6	
Junction and Storage Temperature Range	$T_J, T_{STG}$	-55 to 150	-55 to 150	$^\circ C$

**Thermal Characteristics: n-channel and p-channel**

Parameter		Symbol	Device	Typ	Max	Units
Maximum Junction-to-Ambient <sup>A</sup>	$t \leq 10s$	$R_{\theta JA}$	n-ch	37	50	$^\circ C/W$
	Steady-State		n-ch	74	90	$^\circ C/W$
Maximum Junction-to-Lead <sup>C</sup>	Steady-State	$R_{\theta JL}$	n-ch	28	40	$^\circ C/W$
Maximum Junction-to-Ambient <sup>A</sup>	$t \leq 10s$	$R_{\theta JA}$	p-ch	35	50	$^\circ C/W$
	Steady-State		p-ch	73	90	$^\circ C/W$
Maximum Junction-to-Lead <sup>C</sup>	Steady-State	$R_{\theta JL}$	p-ch	32	40	$^\circ C/W$



AOP607

**N Channel Electrical Characteristics (T<sub>J</sub>=25°C unless otherwise noted)**

Symbol	Parameter	Conditions	Min	Typ	Max	Units
<b>STATIC PARAMETERS</b>						
BV <sub>DSS</sub>	Drain-Source Breakdown Voltage	I <sub>D</sub> =250μA, V <sub>GS</sub> =0V	60			V
I <sub>DSS</sub>	Zero Gate Voltage Drain Current	V <sub>DS</sub> =48V, V <sub>GS</sub> =0V T <sub>J</sub> =55°C			1 5	μA
I <sub>GSS</sub>	Gate-Body leakage current	V <sub>DS</sub> =0V, V <sub>GS</sub> = ±20V			100	nA
V <sub>GS(th)</sub>	Gate Threshold Voltage	V <sub>DS</sub> =V <sub>GS</sub> I <sub>D</sub> =250μA	1.5	2.3	3	V
I <sub>D(ON)</sub>	On state drain current	V <sub>GS</sub> =10V, V <sub>DS</sub> =5V	20			A
R <sub>DS(ON)</sub>	Static Drain-Source On-Resistance	V <sub>GS</sub> =10V, I <sub>D</sub> =4.7A T <sub>J</sub> =125°C		42 75	56	mΩ
		V <sub>GS</sub> =4.5V, I <sub>D</sub> =4A		54	77	mΩ
g <sub>FS</sub>	Forward Transconductance	V <sub>DS</sub> =5V, I <sub>D</sub> =4.7A		11		S
V <sub>SD</sub>	Diode Forward Voltage	I <sub>S</sub> =1A, V <sub>GS</sub> =0V		0.78	1	V
I <sub>S</sub>	Maximum Body-Diode Continuous Current				4	A
<b>DYNAMIC PARAMETERS</b>						
C <sub>iss</sub>	Input Capacitance	V <sub>GS</sub> =0V, V <sub>DS</sub> =30V, f=1MHz		450	540	pF
C <sub>oss</sub>	Output Capacitance			60		pF
C <sub>rss</sub>	Reverse Transfer Capacitance			25		pF
R <sub>g</sub>	Gate resistance	V <sub>GS</sub> =0V, V <sub>DS</sub> =0V, f=1MHz		1.65	2	Ω
<b>SWITCHING PARAMETERS</b>						
Q <sub>g(10V)</sub>	Total Gate Charge	V <sub>GS</sub> =10V, V <sub>DS</sub> =30V, I <sub>D</sub> =4.7A		8.5	10.5	nC
Q <sub>g(4.5V)</sub>	Total Gate Charge			4.3	5.5	nC
Q <sub>gs</sub>	Gate Source Charge			1.6		nC
Q <sub>gd</sub>	Gate Drain Charge			2.2		nC
t <sub>D(on)</sub>	Turn-On DelayTime	V <sub>GS</sub> =10V, V <sub>DS</sub> =30V, R <sub>L</sub> =6Ω, R <sub>GEN</sub> =3Ω		5.1		ns
t <sub>r</sub>	Turn-On Rise Time			2.6		ns
t <sub>D(off)</sub>	Turn-Off DelayTime			15.9		ns
t <sub>f</sub>	Turn-Off Fall Time			2		ns
t <sub>rr</sub>	Body Diode Reverse Recovery Time	I <sub>F</sub> =4.7A, dI/dt=100A/μs		25.1	35	ns
Q <sub>rr</sub>	Body Diode Reverse Recovery Charge	I <sub>F</sub> =4.7A, dI/dt=100A/μs		28.7		nC

A: The value of R<sub>θJA</sub> is measured with the device mounted on 1in<sup>2</sup> FR-4 board with 2oz. Copper, in a still air environment with T<sub>A</sub>=25°C. The value in any given application depends on the user's specific board design. The current rating is based on the t ≤ 10s thermal resistance rating.

B: Repetitive rating, pulse width limited by junction temperature.

C: The R<sub>θJA</sub> is the sum of the thermal impedance from junction to lead R<sub>θJL</sub> and lead to ambient.

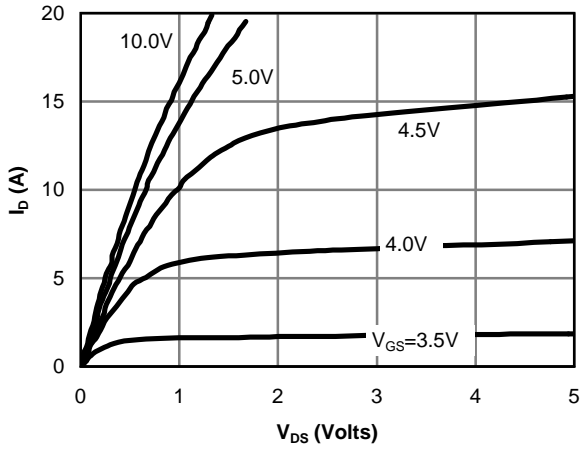
D: The static characteristics in Figures 1 to 6 are obtained using 80μs pulses, duty cycle 0.5% max.

E: These tests are performed with the device mounted on 1 in<sup>2</sup> FR-4 board with 2oz. Copper, in a still air environment with T<sub>A</sub>=25°C. The SOA curve provides a single pulse rating.

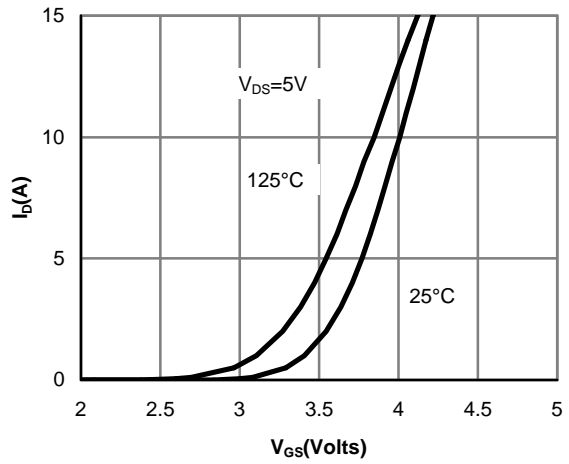
Rev 1 : Aug 2005

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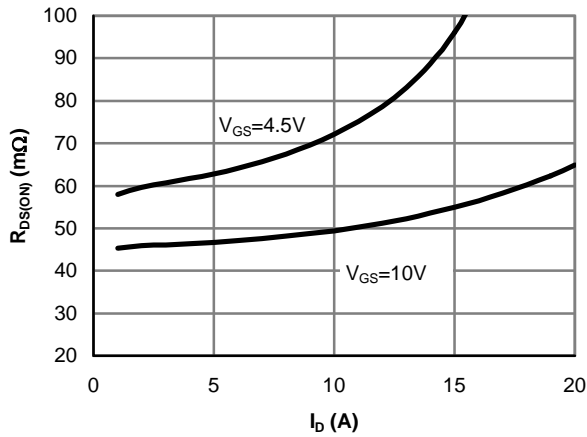
**TYPICAL ELECTRICAL AND THERMAL CHARACTERISTICS: N-CANNEL**



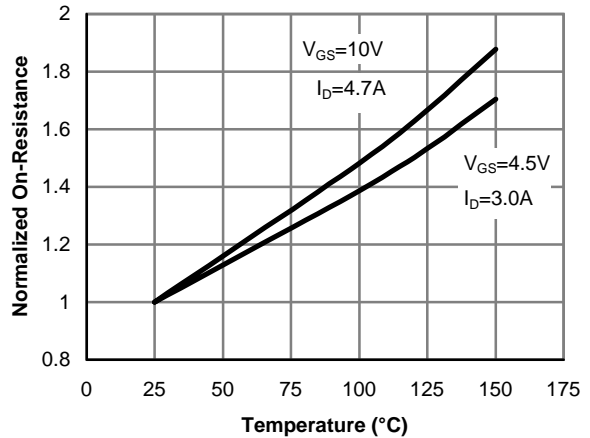
**Fig 1: On-Region Characteristics**



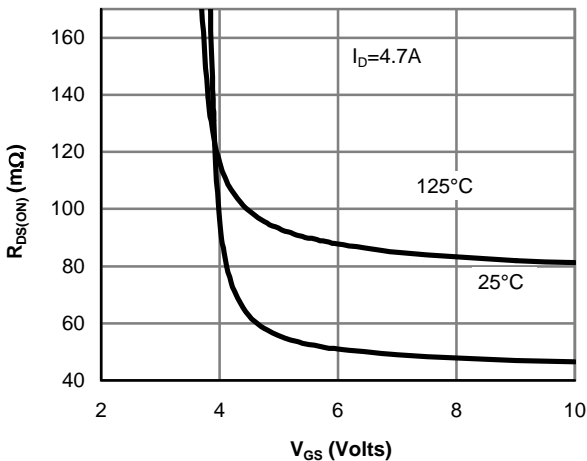
**Figure 2: Transfer Characteristics**



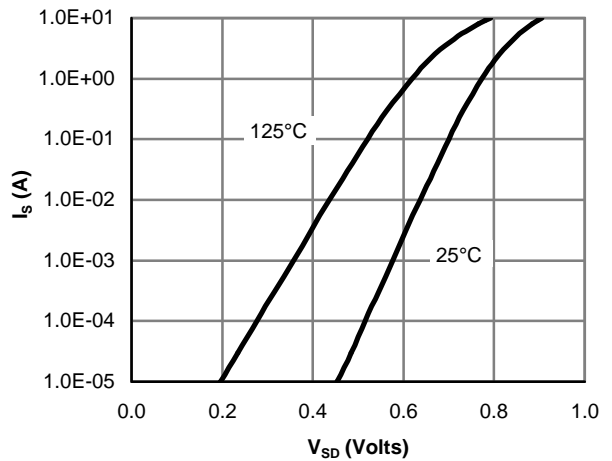
**Figure 3: On-Resistance vs. Drain Current and Gate Voltage**



**Figure 4: On-Resistance vs. Junction Temperature**



**Figure 5: On-Resistance vs. Gate-Source Voltage**



**Figure 6: Body-Diode Characteristics**

TYPICAL ELECTRICAL AND THERMAL CHARACTERISTICS: N-CHANNEL

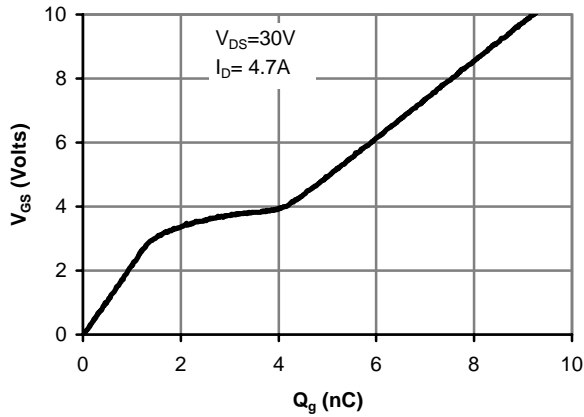


Figure 7: Gate-Charge Characteristics

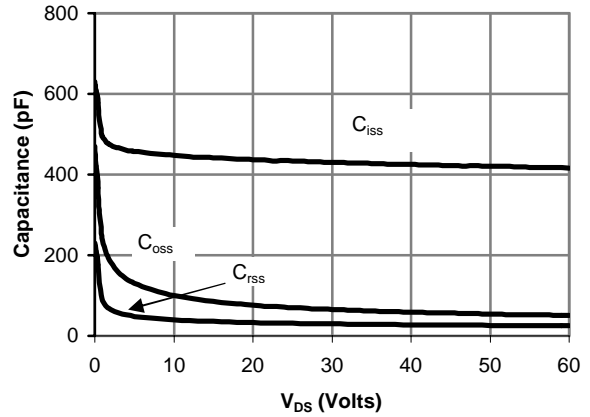


Figure 8: Capacitance Characteristics

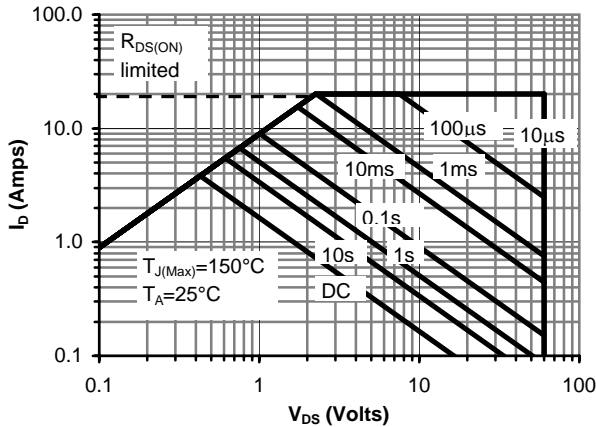


Figure 9: Maximum Forward Biased Safe Operating Area (Note E)

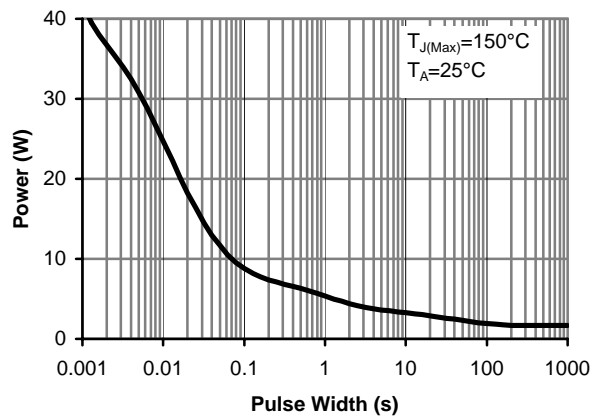


Figure 10: Single Pulse Power Rating Junction-to-Ambient (Note E)

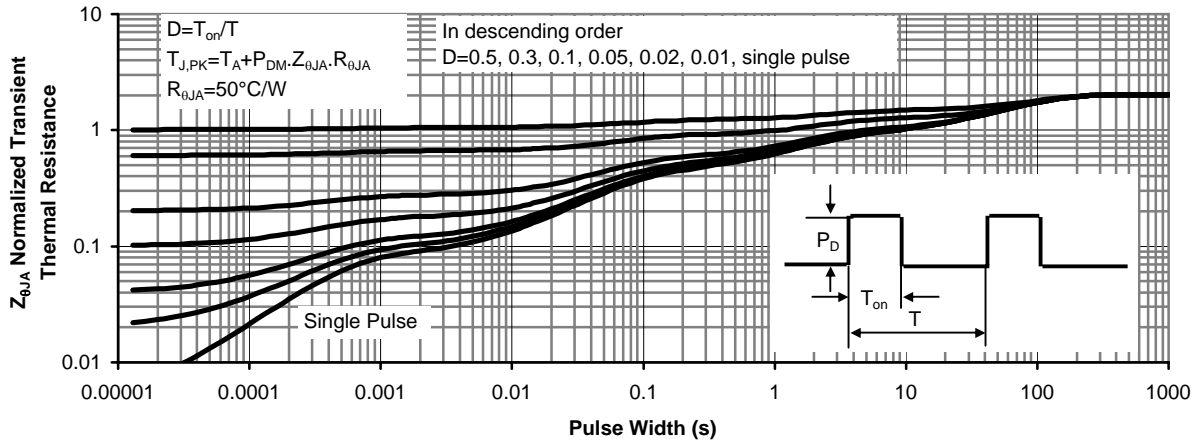


Figure 11: Normalized Maximum Transient Thermal Impedance

**AOP607**

**P-Channel Electrical Characteristics (T<sub>J</sub>=25°C unless otherwise noted)**

Symbol	Parameter	Conditions	Min	Typ	Max	Units
<b>STATIC PARAMETERS</b>						
BV <sub>DSS</sub>	Drain-Source Breakdown Voltage	I <sub>D</sub> =-250μA, V <sub>GS</sub> =0V	-60			V
I <sub>DSS</sub>	Zero Gate Voltage Drain Current	V <sub>DS</sub> =-48V, V <sub>GS</sub> =0V T <sub>J</sub> =55°C			-1 -5	μA
I <sub>GSS</sub>	Gate-Body leakage current	V <sub>DS</sub> =0V, V <sub>GS</sub> =±20V			±100	nA
V <sub>GS(th)</sub>	Gate Threshold Voltage	V <sub>DS</sub> =V <sub>GS</sub> , I <sub>D</sub> =-250μA	-1.5	-2.1	-3	V
I <sub>D(ON)</sub>	On state drain current	V <sub>GS</sub> =-10V, V <sub>DS</sub> =-5V	-20			A
R <sub>DS(ON)</sub>	Static Drain-Source On-Resistance	V <sub>GS</sub> =-10V, I <sub>D</sub> =-3.4A T <sub>J</sub> =125°C		80	105	mΩ
		V <sub>GS</sub> =-4.5V, I <sub>D</sub> =-2.7A		130		mΩ
				102	135	mΩ
g <sub>FS</sub>	Forward Transconductance	V <sub>DS</sub> =-5V, I <sub>D</sub> =-3.4A		10		S
V <sub>SD</sub>	Diode Forward Voltage	I <sub>S</sub> =-1A, V <sub>GS</sub> =0V		-0.77	-1	V
I <sub>S</sub>	Maximum Body-Diode Continuous Current				-4	A
<b>DYNAMIC PARAMETERS</b>						
C <sub>iss</sub>	Input Capacitance	V <sub>GS</sub> =0V, V <sub>DS</sub> =-30V, f=1MHz		930	1120	pF
C <sub>oss</sub>	Output Capacitance			85		pF
C <sub>rss</sub>	Reverse Transfer Capacitance			35		pF
R <sub>g</sub>	Gate resistance	V <sub>GS</sub> =0V, V <sub>DS</sub> =0V, f=1MHz		7.2	9	Ω
<b>SWITCHING PARAMETERS</b>						
Q <sub>g(10V)</sub>	Total Gate Charge (10V)	V <sub>GS</sub> =-10V, V <sub>DS</sub> =-30V, I <sub>D</sub> =-3.4A		16	20	nC
Q <sub>g(4.5V)</sub>	Total Gate Charge (4.5V)			8	10	nC
Q <sub>gs</sub>	Gate Source Charge			2.5		nC
Q <sub>gd</sub>	Gate Drain Charge			3.2		nC
t <sub>D(on)</sub>	Turn-On DelayTime	V <sub>GS</sub> =-10V, V <sub>DS</sub> =-30V, R <sub>L</sub> =8.8Ω, R <sub>GEN</sub> =3Ω		8		ns
t <sub>r</sub>	Turn-On Rise Time			3.8		ns
t <sub>D(off)</sub>	Turn-Off DelayTime			31.5		ns
t <sub>f</sub>	Turn-Off Fall Time			7.5		ns
t <sub>rr</sub>	Body Diode Reverse Recovery Time	I <sub>F</sub> =-3.4A, dI/dt=100A/μs		27	35	ns
Q <sub>rr</sub>	Body Diode Reverse Recovery Charge	I <sub>F</sub> =-3.4A, dI/dt=100A/μs		32		nC

A: The value of R<sub>θJA</sub> is measured with the device mounted on 1in<sup>2</sup> FR-4 board with 2oz. Copper, in a still air environment with T<sub>A</sub>=25°C. The value in any given application depends on the user's specific board design. The current rating is based on the ≤ 10s thermal resistance rating.  
 B: Repetitive rating, pulse width limited by junction temperature.  
 C: The R<sub>θJA</sub> is the sum of the thermal impedance from junction to lead R<sub>θJL</sub> and lead to ambient.  
 D: The static characteristics in Figures 1 to 6,12,14 are obtained using 80μs pulses, duty cycle 0.5% max.  
 E: These tests are performed with the device mounted on 1 in<sup>2</sup> FR-4 board with 2oz. Copper, in a still air environment with T<sub>A</sub>=25°C. The SOA curve provides a single pulse rating.  
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TYPICAL ELECTRICAL AND THERMAL CHARACTERISTICS: P-CHANNEL

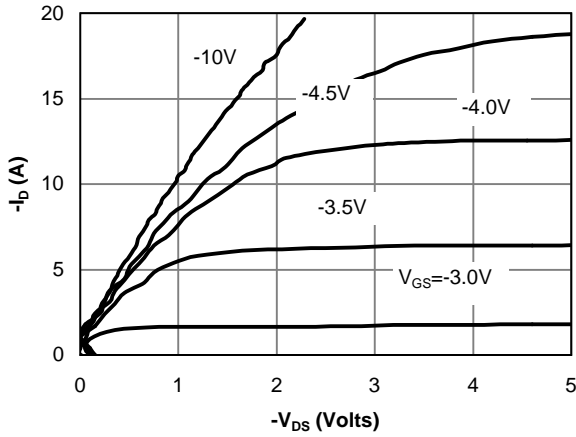


Fig 1: On-Region Characteristics

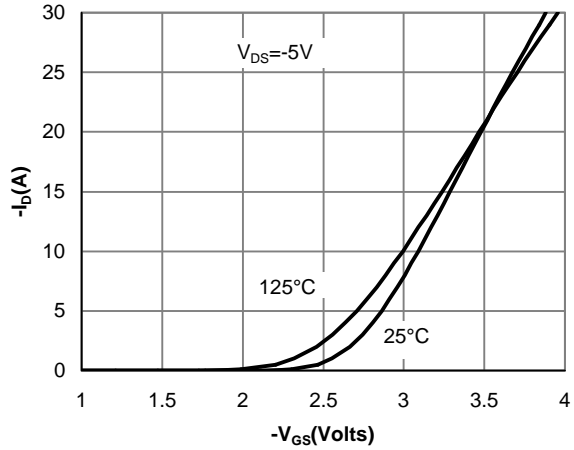


Figure 2: Transfer Characteristics

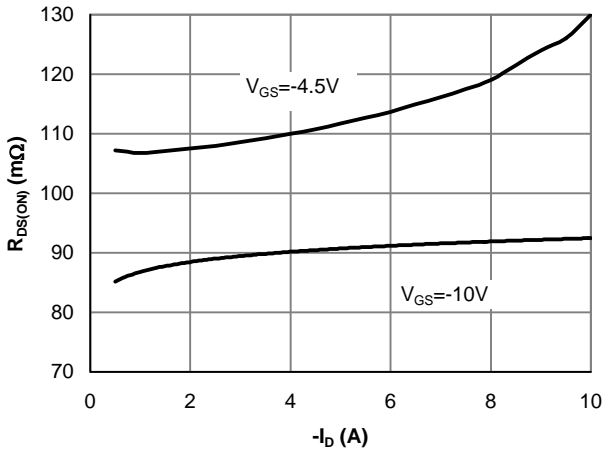


Figure 3: On-Resistance vs. Drain Current and Gate Voltage

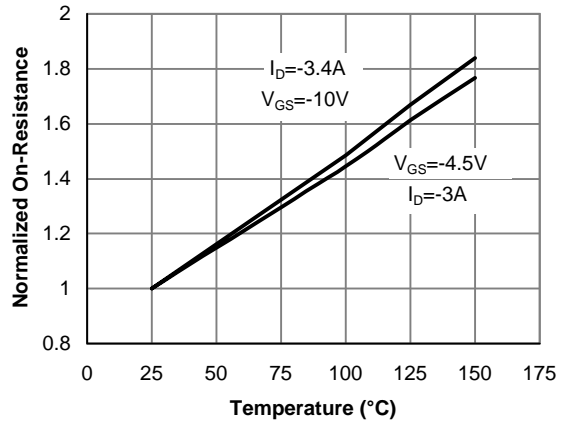


Figure 4: On-Resistance vs. Junction Temperature

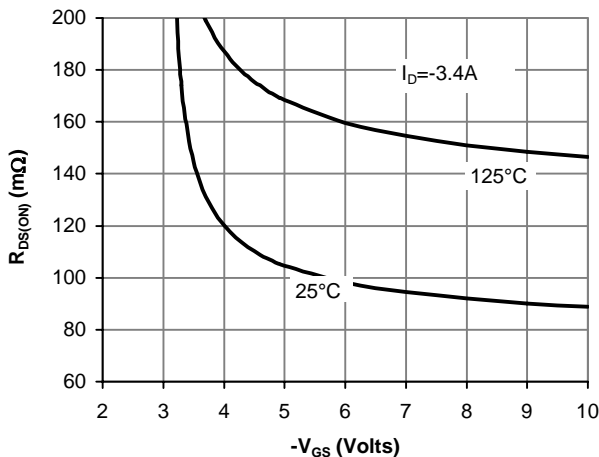


Figure 5: On-Resistance vs. Gate-Source Voltage

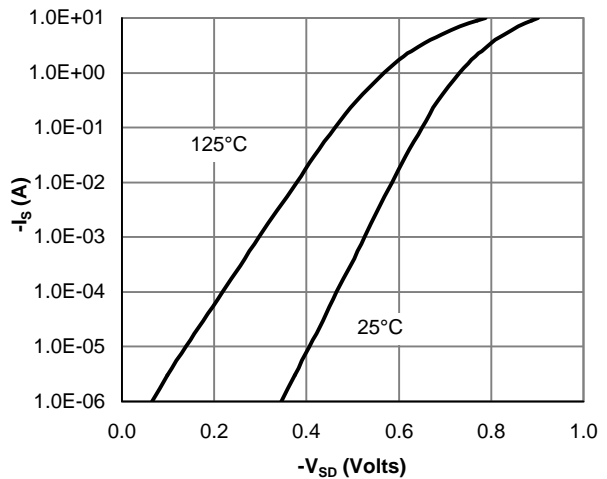


Figure 6: Body-Diode Characteristics

TYPICAL ELECTRICAL AND THERMAL CHARACTERISTICS: P-CHANNEL

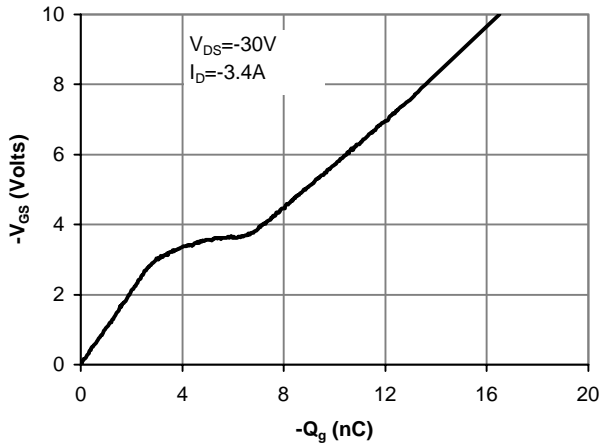


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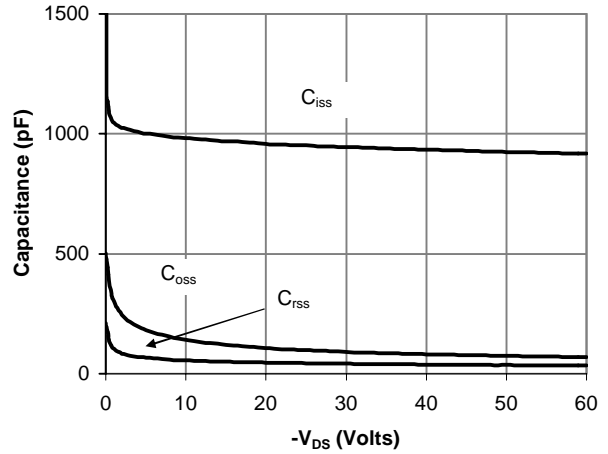


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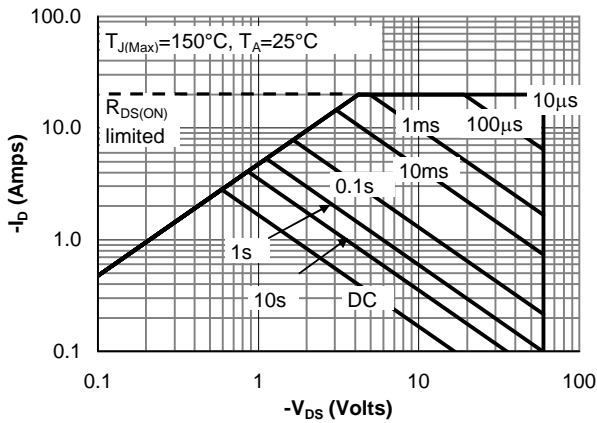


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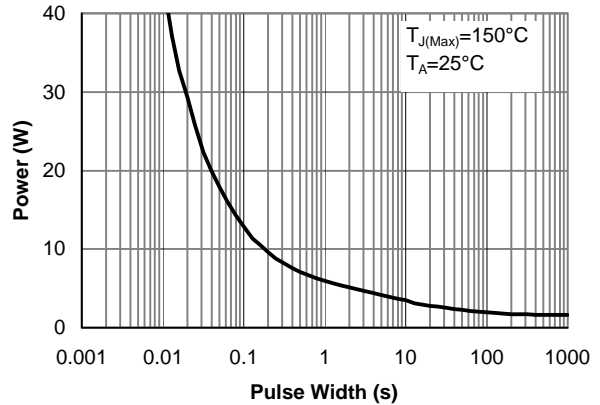


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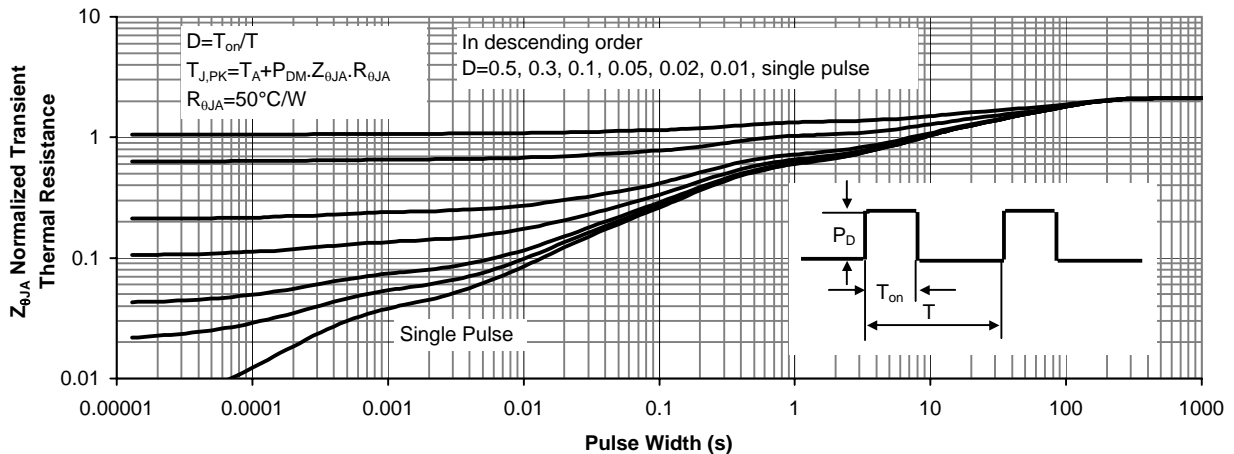


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